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Data Sheet

#### September 2013

## N-Channel Power MOSFET 60V, 70A, 14 $m\Omega$

These are N-Channel power MOSFETs manufactured using the MegaFET process. This process, which uses feature sizes approaching those of LSI circuits, gives optimum utilization of silicon, resulting in outstanding performance. They were designed for use in applications such as switching regulators, switching converters, motor drivers and relay drivers. These transistors can be operated directly from integrated circuits.

Formerly developmental type TA78440.

#### **Ordering Information**

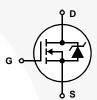
PART NUMBER	PACKAGE	BRAND		
RFP70N06	TO-220AB	RFP70N06		

NOTE: When ordering use the entire part number. Add the suffix 9A to obtain the TO-263AB variant in tape and reel, e.g. RF1S70N06SM9A.

#### **Features**

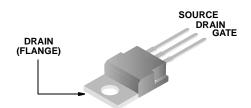
- 70A, 60V
- $r_{DS(on)} = 0.014\Omega$
- Temperature Compensated PSPICE<sup>®</sup> Model
- Peak Current vs Pulse Width Curve
- UIS Rating Curve (Single Pulse)
- 175°C Operating Temperature
- · Related Literature
  - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

#### Symbol



### Packaging

#### JEDEC TO-220AB



#### RFP70N06

#### **Absolute Maximum Ratings** $T_C = 25^{\circ}C$ , Unless Otherwise Specified

	RFP70N06	UNITS
Drain to Source Voltage (Note 1)VDSS	60	V
Drain to Gate Voltage ( $R_{GS} = 20k\Omega$ ) (Note 1)	60	V
Continuous Drain Current	70	Α
Pulsed Drain Current (Note 3)	Refer to Peak Current Curve	
Gate to Source Voltage	±20	V
Single Pulse Avalanche Rating	Refer to UIS Curve	Α
Power Dissipation	150	W
Linear Derating Factor	1.0	W/oC
Operating and Storage Temperature	-55 to 175	οС
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10sT <sub>L</sub>	300	oC
Package Body for 10s, See Techbrief 334	260	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

#### NOTE:

1.  $T_J = 25^{\circ}C$  to  $150^{\circ}C$ .

#### **Electrical Specifications** $T_C = 25^{\circ}C$ , Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V (Figure 11)	60	-	-	V
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250μA (Figure 10)	2	-	4	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V	-	-	1	μΑ
		$V_{DS} = 0.8 \text{ x Rated BV}_{DSS}, T_{C} = 150^{\circ}\text{C}$	-	-	25	μΑ
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V	-	-	±100	nA
Drain to Source On Resistance (Note 2)	r <sub>DS(ON)</sub>	I <sub>D</sub> = 70A, V <sub>GS</sub> = 10V (Figure 9)	-	-	0.014	Ω
Turn-On Time	t(ON)	$V_{DD} = 30V, I_{D} \approx 70A, R_{L} = 0.43\Omega,$ $V_{GS} = 10V, R_{GS} = 2.5\Omega$ (Figure 13)	-	-	190	ns
Turn-On Delay Time	t <sub>d</sub> (ON)		-	10	-	ns
Rise Time	t <sub>r</sub>		-	137	-	ns
Turn-Off Delay Time	t <sub>d</sub> (OFF)		-	32	-	ns
Fall Time	t <sub>f</sub>		-	24	-	ns
Turn-Off Time	t(OFF)		-	-	73	ns
Total Gate Charge	Q <sub>g(TOT)</sub>	$V_{GS} = 0V \text{ to } 20V$ $V_{DD} = 48V, I_D = 70A,$	-	120	156	nC
Gate Charge at 10V	Q <sub>g(10)</sub>	$V_{GS} = 0V \text{ to } 10V$ $R_L = 0.68\Omega$ $I_{g(REF)} = 2.2\text{mA}$	-	65	85	nC
Threshold Gate Charge	Q <sub>g(TH)</sub>	$V_{GS} = 0V \text{ to } 2V$ (Figure 13)	-	5.0	6.5	nC
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz	-	2250	-	pF
Output Capacitance	C <sub>OSS</sub>	(Figure 12)	-	792	-	pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			206	-	pF
Thermal Resistance, Junction to Case	$R_{ heta JC}$		-	-	1.0	°C/W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	TO-220		-	62	°C/W
		-	-	-	-	-

#### **Source to Drain Diode Specifications**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	$V_{SD}$	I <sub>SD</sub> = 70A		-	1.5	V
Reverse Recovery Time	t <sub>rr</sub>	$I_{SD} = 70A$ , $dI_{SD}/dt = 100A/\mu s$		-	52	ns

#### NOTES:

- 2. Pulse test: pulse width ≤300ms, duty cycle ≤2%.
- 3. Repetitive rating: pulse width is limited by maximum junction temperature. See Transient Thermal Impedance curve (Figure 3) and Peak Current Capability Curve (Figure 5).

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#### **Typical Performance Curves** T<sub>C</sub> = 25°C, Unless Otherwise Specified

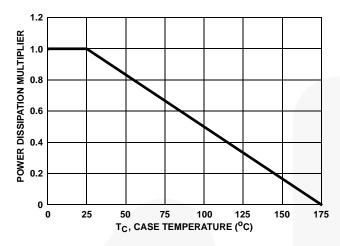


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

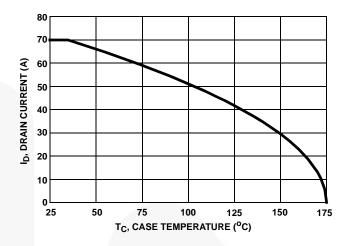


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

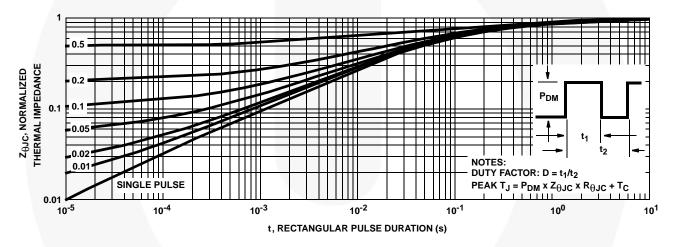


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

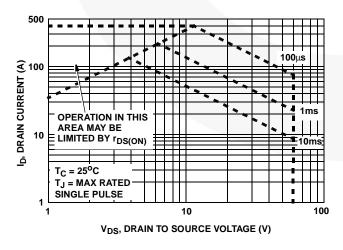


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

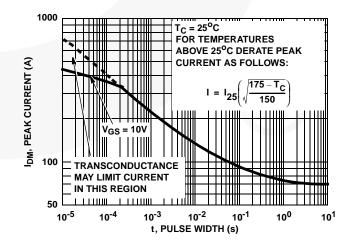
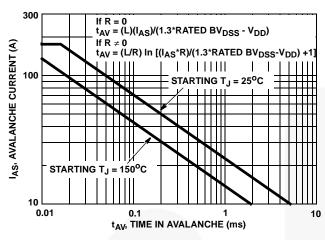


FIGURE 5. PEAK CURRENT CAPABILITY

#### Typical Performance Curves T<sub>C</sub> = 25°C, Unless Otherwise Specified (Continued)



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.

FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING CAPABILITY

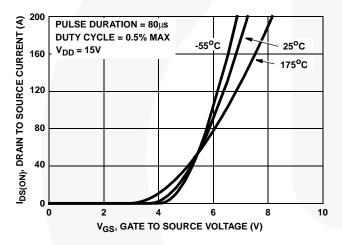


FIGURE 8. TRANSFER CHARACTERISTICS

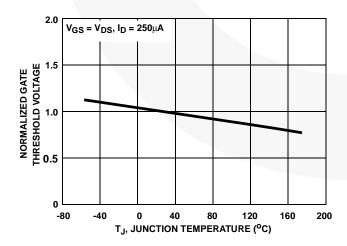


FIGURE 10. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

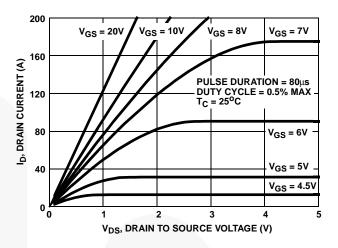


FIGURE 7. SATURATION CHARACTERISTICS

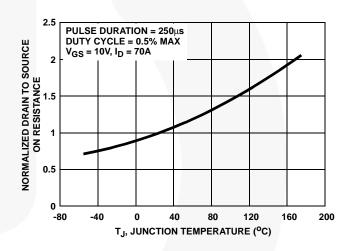


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

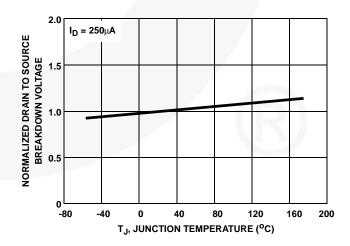


FIGURE 11. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

### **Typical Performance Curves** T<sub>C</sub> = 25°C, Unless Otherwise Specified (Continued)

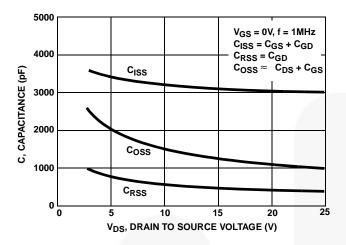
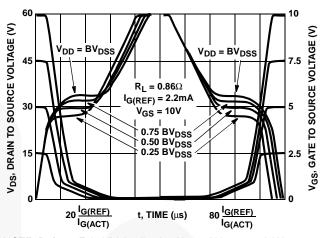


FIGURE 12. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 13. NORMALIZED SWITCHING WAVEFORMS FOR CONSTANT GATE CURRENT

#### Test Circuits and Waveforms

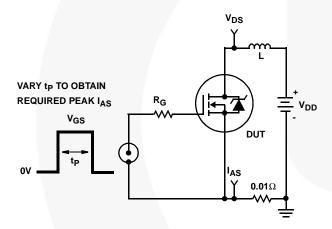


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

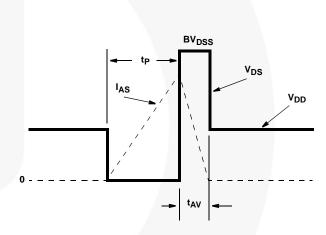


FIGURE 15. UNCLAMPED ENERGY WAVEFORMS

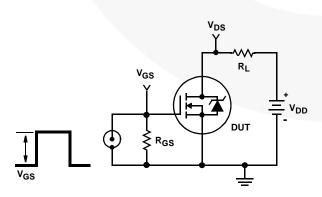


FIGURE 16. SWITCHING TIME TEST CIRCUIT

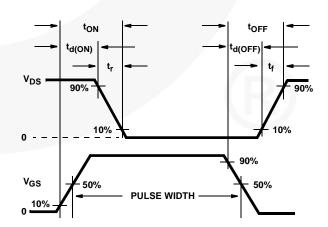


FIGURE 17. SWITCHING WAVEFORMS

## Test Circuits and Waveforms (Continued)

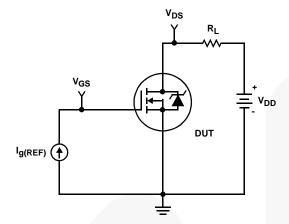


FIGURE 18. GATE CHARGE TEST CIRCUIT

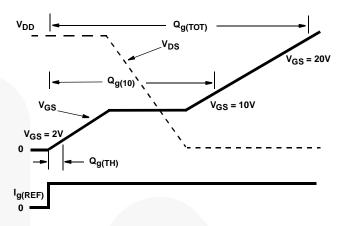


FIGURE 19. GATE CHARGE WAVEFORM

#### **PSPICE Electrical Model**

.SUBCKT RFG70N06 213: rev 3/20/92 CA 12 8 5.56e-9 RLDRAIN CB 15 14 5.30e-9 **DPLCAP** CIN 6 8 2.63e-9 10 DRAIN LDRAIN DBODY 7 5 DBDMOD DBREAK 5 11 DBKMOD RSCL2 ≷ RSCL1 DBREAK T DPLCAP 10 5 DPLCAPMOD + 51 **ESCL** EBREAK 11 7 17 18 65.18 DBODY 50 EDS 14 8 5 8 1 **RDRAIN** EGS 13 8 6 8 1 **ESG EBREAK** VTO + 16 ESG 6 10 6 8 1 EVTO 20 6 18 8 1 RLGATE MOS<sub>2</sub> ⊣∐⊦ **EVTO GATE** 20. 6 18 8 IT 8 17 1 MOS1 **RGATE LGATE** LDRAIN 2 5 1e-9 RIN CIN RLSOURCE LGATE 1 9 3.10e-9 RSOURCE 8 LSOURCE 3 7 1.82e-9 03 SOURCE MOS1 16 6 8 8 MOSMOD M = 0.99 LSOURCE S1A S2A MOS2 16 21 8 8 MOSMOD M = 0.01 **RBREAK** 12 14 13 17 18 8 13 RBREAK 17 18 RBKMOD 1 RDRAIN 50 16 RDSMOD 4.66e-3 S1B S2B RVTO RLDRAIN 2 5 10 13 CA CB 19 RGATE 9 20 1.21  $\bigcirc$ IT VBAT RLGATE 1 9 31 **EGS** FDS RIN 6 8 1e9 RSOURCE 8 7 RDSMOD 3.92e-3 RLSOURCE 3 7 18.2 RVTO 18 19 RVTOMOD 1 S1A 6 12 13 8 S1AMOD S1B 13 12 13 8 S1BMOD S2A 6 15 14 13 S2AMOD S2B 13 15 14 13 S2BMOD VBAT 8 19 DC 1 VTO 21 6 0.605 .MODEL DBDMOD D (IS = 7.91e-12 RS = 3.87e-3 TRS1 = 2.71e-3 TRS2 = 2.50e-7 CJO = 4.84e-9 TT = 4.51e-8) .MODEL DBKMOD D (RS = 3.9e-2 TRS1 =1.05e-4 TRS2 = 3.11e-5) .MODEL DPLCAPMOD D (CJO = 4.8e-9 IS = 1e-30 N = 10) .MODEL MOSMOD NMOS (VTO = 3.46 KP = 47 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u) .MODEL RBKMOD RES (TC1 = 8.46e-4 TC2 = -8.48e-7) .MODEL RDSMOD RES (TC1 = 2.23e-3 TC2 = 6.56e-6) .MODEL RVTOMOD RES (TC1 = -3.29e-3 TC2 = 3.49e-7) .MODEL S1AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -8.35 VOFF= -6.35) .MODEL S1BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -6.35 VOFF= -8.35) .MODEL S2AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -2.0 VOFF= 3.0) .MODEL S2BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 3.0 VOFF= -2.0)

NOTE: For further discussion of the PSPICE model, consult **A New PSPICE Sub-circuit for the Power MOSFET Featuring Global Temperature Options**; written by William J. Hepp and C. Frank Wheatley.

.ENDS





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